

# AH118

## ¼ Watt, High Linearity InGaP HBT Amplifier



### Applications

- Final stage amplifiers for Repeaters
- Mobile Infrastructure

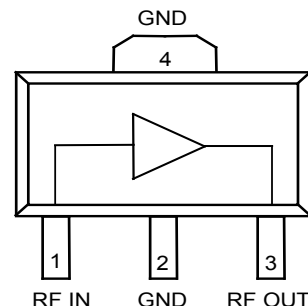


SOT-89 Package

### Product Features

- 60 – 3500 MHz
- +24.7 dBm P1dB
- +40.5 dBm Output IP3
- 20.4 dB Gain @ 900 MHz
- 16.5 dB Gain @ 1900 MHz
- +5V Single Positive Supply
- Lead-free/Green/RoHS-compliant SOT-89 Package

### Functional Block Diagram



### General Description

The AH118 is a high dynamic range driver amplifier in a low-cost surface mount package. The InGaP/GaAs HBT is able to achieve high performance across a broad range with +40.5 dBm OIP3 and +24.7 dBm of compressed 1dB power. The AH118 is available in a lead-free/green/RoHS-compliant SOT-89 package. All devices are 100% RF and DC tested.

The AH118 is targeted for use as a driver amplifier in wireless infrastructure where high linearity and medium power is required. Internal biasing allows the AH118 to maintain high linearity over temperature and operate directly off a single +5V supply. This combination makes the device an excellent candidate for transceiver line cards in current and next generation multi-carrier 3G base stations.

### Pin Configuration

Pin #	Function
1	Input / Base
2	Ground
3	Output / Collector
4	Ground

**Not Recommended for New Designs**

Recommended Replacement Part: TQP7M9101

### Ordering Information

Part No.	Description
AH118-89G	High IP3 InGaP HBT Amp

Standard T/R size = 1000 pieces on a 7" reel.

# AH118

¼ Watt, High Linearity InGaP HBT Amplifier



## Specifications

### Absolute Maximum Ratings

Parameter	Rating
Storage Temperature	-65 to +150 °C
RF Input Power, T = 25°C	+15 dBm
Device Voltage	+6 V
Device Current	220 mA

Operation of this device outside the parameter ranges given above may cause permanent damage.

### Recommended Operating Conditions

Parameter	Min	Typ	Max	Units
V <sub>cc</sub>	+4.75	+5	+5.25	V
I <sub>cc</sub>		160		mA
T <sub>J</sub> (for >10 <sup>6</sup> hours MTF)			200	°C

Electrical specifications are measured at specified test conditions. Specifications are not guaranteed over all recommended operating conditions.

## Electrical Specifications

Test conditions unless otherwise noted: +25°C on a tuned test fixture

Parameter	Conditions	Min	Typical	Max	Units
Operational Frequency Range		60		3500	MHz
Test Frequency			1900		MHz
Gain		13.5	16.0		dB
Input Return Loss			12		dB
Output Return Loss			20		dB
Output P1dB		+23	+24.7		dBm
Output IP3	See Note 1	+39.5	+40.5		dBm
WCDMA Channel Power @ -45 dBc ACLR, 2140 MHz	See Note 2		+16.7		dBm
Noise Figure			4.3		dB
V <sub>cc</sub>			+5		V
Operational Current Range		140	160	175	mA
Thermal Resistance (junction to case)				92	°C/W

Notes:

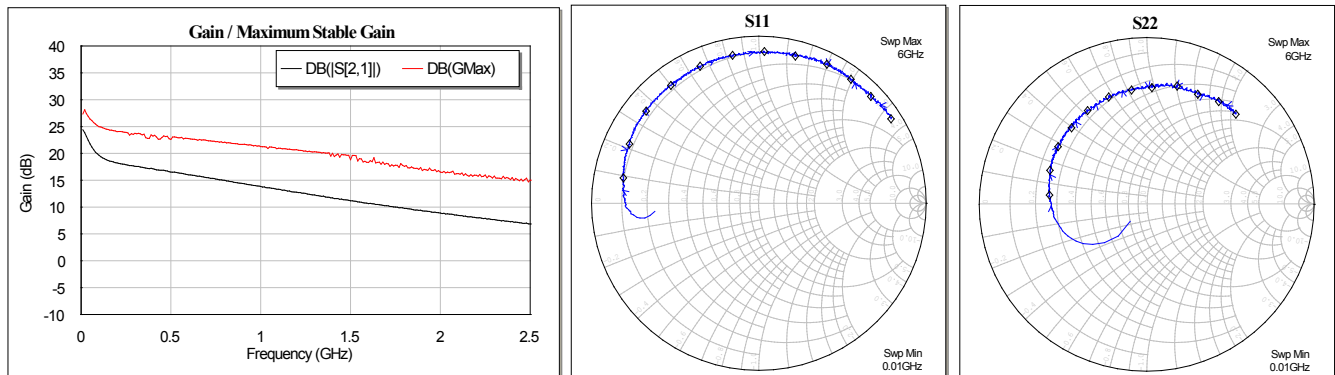
- OIP3 is measured with two tones separated by 1 MHz at 11dBm output power/tone. The suppression on the largest IM3 product is used to calculate the OIP3 using a 2:1 rule.
- Signal: W-CDMA 3GPP Test Model 1+64 DPCH, PAR = 10 dB @ 0.01% Probability, 3.84 MHz BW

# AH118

## 1/4 Watt, High Linearity InGaP HBT Amplifier



### Device Characterization Data



Note:

1. S-Parameters ( $V_{Device} = +5\text{ V}$ ,  $I_{CC} = 160\text{ mA}$ ,  $25\text{ }^{\circ}\text{C}$ , unmatched 50 ohm system).
2. The gain for the unmatched device in 50 ohm system is shown as the trace in black color. For a tuned circuit for a particular frequency, it is expected that actual gain will be higher, up to the maximum stable gain. The maximum stable gain is shown in the dashed red line.
3. The impedance plots are shown from 0.5 – 6 GHz, with markers placed at 0.5 – 6.0 GHz in 0.5 GHz increments.

### S-Parameter Data

$V_{cc} = +5\text{ V}$ ,  $I_{cd} = 160\text{ mA}$ ,  $T = 25\text{ }^{\circ}\text{C}$ , unmatched 50 Ohm system, calibrated to device leads

Freq (MHz)	S11 (dB)	S11 (ang)	S21 (dB)	S21 (ang)	S12 (dB)	S12 (angle)	S22 (dB)	S22 (ang)
50	-2.69	-173.38	21.74	153.70	-31.02	11.24	-7.02	-148.17
100	-2.16	-177.19	19.63	150.82	-30.31	7.90	-5.57	-162.45
200	-1.91	178.30	18.22	148.19	-29.87	5.01	-5.06	-173.51
400	-1.77	172.47	17.13	135.41	-29.83	4.07	-4.77	177.87
600	-1.60	166.83	15.99	121.91	-29.49	2.79	-4.60	171.65
800	-1.45	161.09	14.97	109.02	-29.18	2.11	-4.44	166.08
1000	-1.40	155.39	13.84	97.28	-28.70	1.64	-4.26	160.40
1200	-1.25	149.59	12.76	86.83	-28.63	-0.09	-4.14	155.01
1400	-1.20	143.79	11.71	76.95	-28.30	-1.34	-3.97	149.63
1600	-1.17	137.57	10.63	68.15	-27.94	-4.47	-4.00	144.03
1800	-1.13	132.05	9.75	59.55	-27.63	-7.00	-3.86	139.02
2000	-1.11	126.72	8.88	52.22	-27.51	-8.43	-3.84	134.24
2200	-1.05	121.50	8.00	45.09	-27.06	-11.00	-3.62	129.30
2400	-0.99	115.58	7.31	37.40	-27.02	-14.19	-3.55	124.42
2600	-0.93	110.41	6.52	30.66	-26.78	-18.24	-3.46	119.42
2800	-0.95	105.30	5.73	23.51	-26.66	-20.10	-3.34	114.26
3000	-0.92	100.11	5.05	17.07	-26.61	-23.28	-3.30	109.29

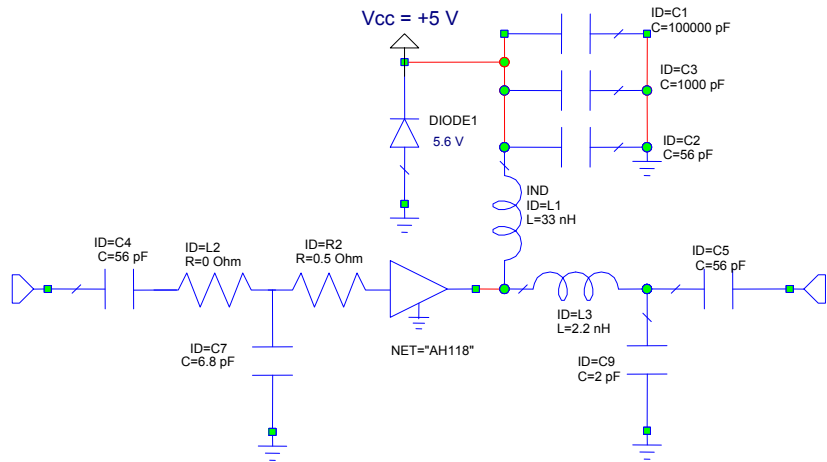
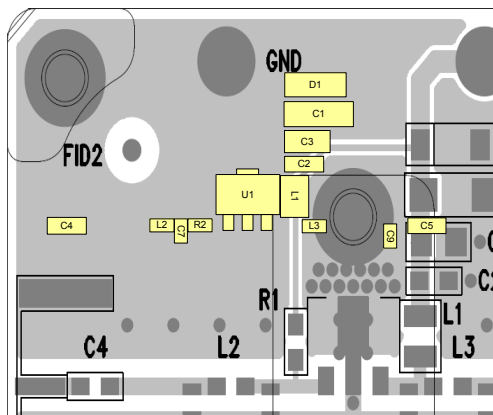
Device S-parameters are available for download off of the website at: <http://www.triquint.com>

# AH118

1/4 Watt, High Linearity InGaP HBT Amplifier



## Reference Design 920-960 MHz (AH118-89PCB900)



### Notes:

1. The diode D1 is used as over-voltage protection on the evaluation boards. It is not specifically required in the final circuit layout in a system using a DC regulator.
2. L2 - the 0  $\Omega$  resistor - can be removed (with a thru line) in the final circuit layout.
3. The distance from U1 pin1 pad to the edge of C7 is 120 mil.
4. The distance from U1 pin3 pad to the edge of C9 is 350 mil.

## Bill of Material

Ref Des	Value	Description	Manufacturer	Part Number
U1		High Linearity Amplifier	TriQuint	AH118-89G
C1	0.1 $\mu$ F	Cap, Chip, 1206, 50 V, 10%, X7R	various	
C2, C4, C5	56 pF	Cap, Chip, 0603, 50 V, 5%, NPO/COG	various	
C3	1000 pF	Cap, Chip, 0805, 50 V, 5%, NPO	various	
C7	6.8 pF	Cap, Chip, 0603, 200 V, NPO/COG	various	
C9	2.0 pF	Cap, Chip, 0603, 200 V, NPO/COG	various	
L1	33 nH	Ind, Chip, 0603, 5%, Ceramic Core	various	
L2	0 $\Omega$	Res, Chip, 0603, 5%, 1/16 W	various	
L3	2.2 nH	Ind, Chip, 0603, $\pm$ 0.3 nH, Multilayer	various	
R2	0.51 $\Omega$	Res, Chip, 0603, 5%, 1/10 W	various	
R1		No Load Part		
D1		Zener Diode, SOD-123		

# AH118

## 1/4 Watt, High Linearity InGaP HBT Amplifier

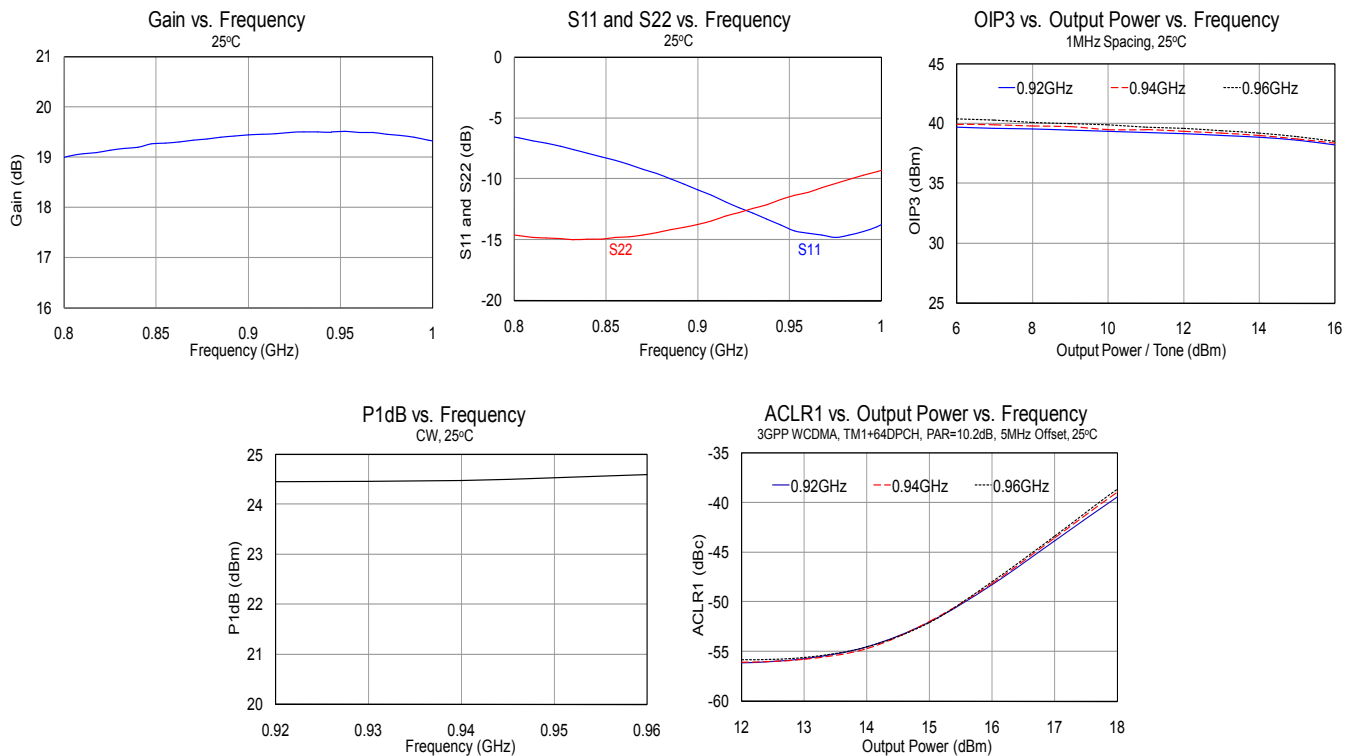


### Typical Performance 920-960 MHz (AH118-89PCB900)

Frequency	MHz	920	940	960
Gain [1]	dB	19.5	19.5	19.5
Input Return Loss	dB	12.5	13.2	14.2
Output Return Loss	dB	12.5	11.7	11.0
Output P1dB	dBm	24.4	24.5	24.6
Output IP3 [2]	dBm	39.3	39.5	39.7
Channel Power @ -45 dBc ACLR [3]	dBm	16.7	16.7	16.7
Noise Figure	dB	4.3	4.4	4.5
Quiescent Current , Icq	mA	160		
Device / Supply Voltage , Vcc	V	+5		

#### Notes

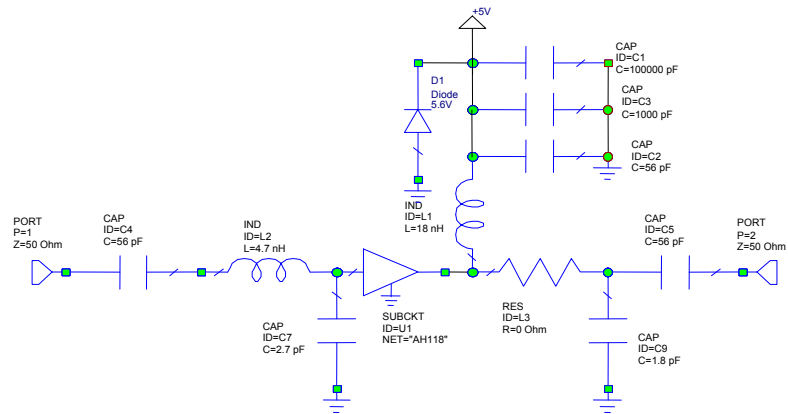
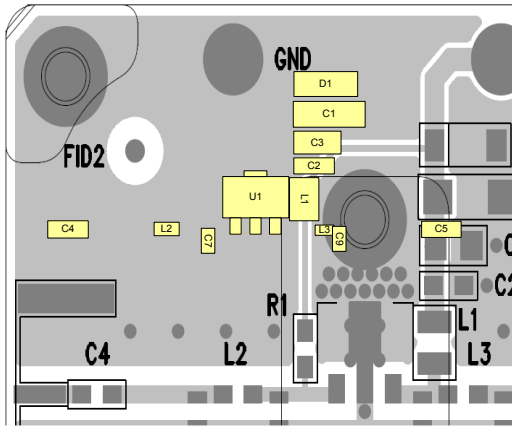
1. Test conditions unless otherwise noted: 25 °C, +5V, in tuned application circuit.
2. OIP3 is measured at 11 dBm Pout / tone with 1 MHz spacing.
3. ACLR test set-up: 3GPP WCDMA, TM1+64DPCH, +5MHz Offset, PAR = 10.2 dB @ 0.01% Probability.



# AH118

¼ Watt, High Linearity InGaP HBT Amplifier

## Reference Design 1900 MHz



**Note:**

1. The diode D1 is used as over-voltage protection on the evaluation boards. It is not specifically required in the final circuit layout in a system using a DC regulator.
2. L2 - the 0 Ω resistor - can be removed (with a thru line) in the final circuit layout.
3. C7 should be placed at the silk screen marker 'B' on the TriQuint evaluation board.
4. C7 should be placed at the silk screen marker '4' on the TriQuint evaluation board.

## Bill of Material

Ref Des	Value	Description	Manufacturer	Part Number
U1		High Linearity Amplifier	TriQuint	AH118-89G
C1	0.1 μF	Cap, Chip, 1206, 50 V, 10%, X7R	various	
C2, C4, C5	56 pF	Cap, Chip, 0603, 50 V, 5%, NPO/COG	various	
C3	1000 pF	Cap, Chip, 0805, 50 V, 5%, NPO	various	
C7	2.7 pF	Cap, Chip, 0603, 50 V, ±0.05 pF, NPO/COG	various	
C9	1.8 pF	Cap, Chip, 0603, 50 V, ±0.05 pF, NPO/COG	various	
L1	18 nH	Ind, Chip, 0603, 5%, Ceramic Core	various	
L2	4.7 nH	Ind, Chip, 0603, ±0.3 nH, Multilayer	various	
L3	0 Ω	Res, 0402, Chip, 5%, 1/16 W	various	
R1		No Load Part		
D1		Zener Diode, SOD-123		

# AH118

## 1/4 Watt, High Linearity InGaP HBT Amplifier

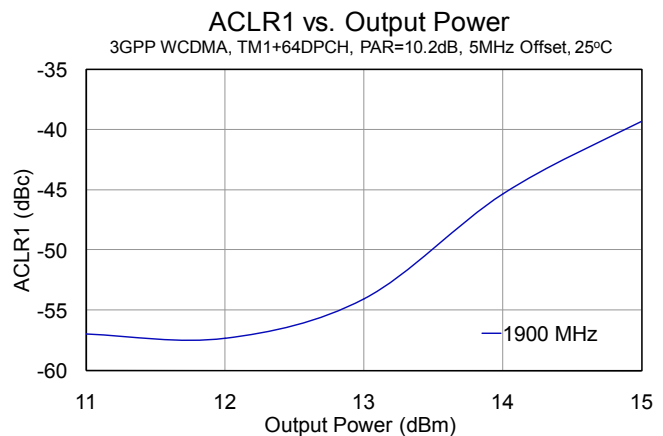
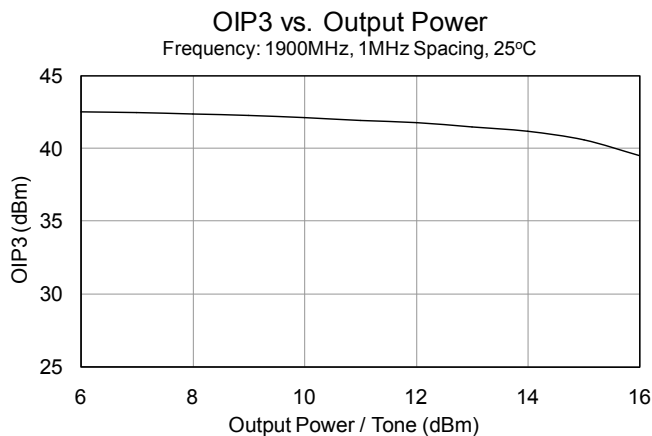
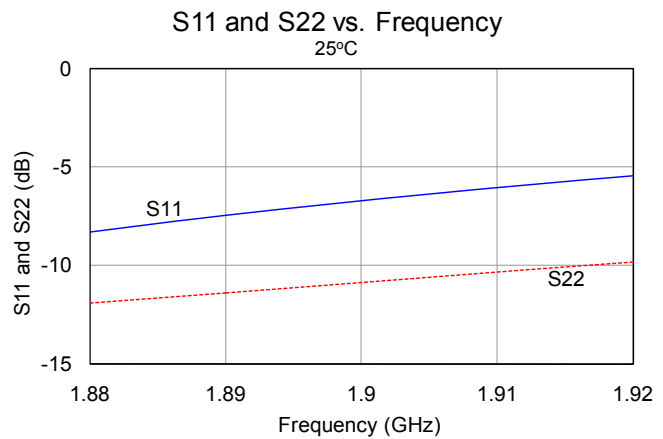
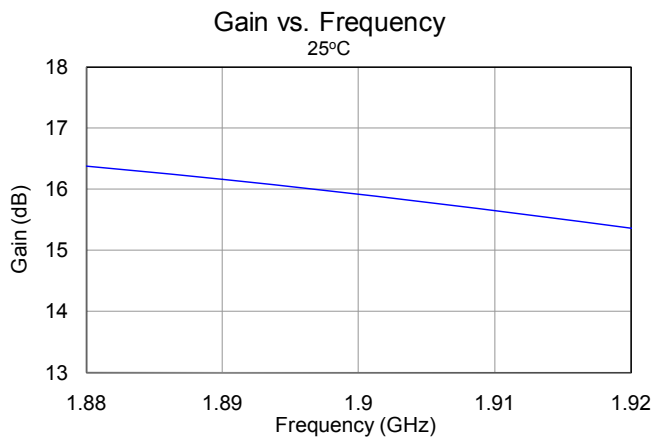


### Typical Performance 1900 MHz

Frequency	MHz	1900
Gain [1]	dB	16.0
Input Return Loss	dB	7.5
Output Return Loss	dB	11.4
Output P1dB	dBm	25.4
Output IP3 [2]	dBm	41.5
Channel Power @ -45 dBc ACLR [3]	dBm	14
Quiescent Current , Icq	mA	160
Device / Supply Voltage , Vcc	V	+5

Notes

1. Test conditions unless otherwise noted: 25 °C, +5V, in tuned application circuit.
2. OIP3 is measured at 11 dBm Pout / tone with 1 MHz spacing.
3. ACLR test set-up: 3GPP WCDMA, TM1+64DPCH, +5MHz Offset, PAR = 10.2 dB @ 0.01% Probability.

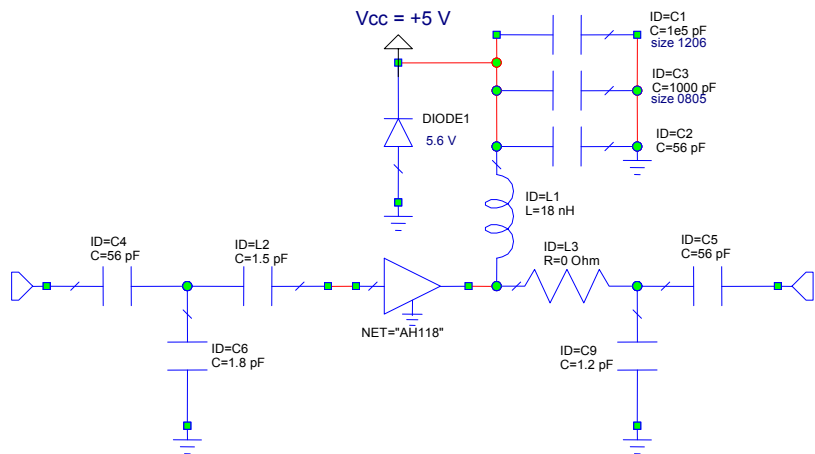
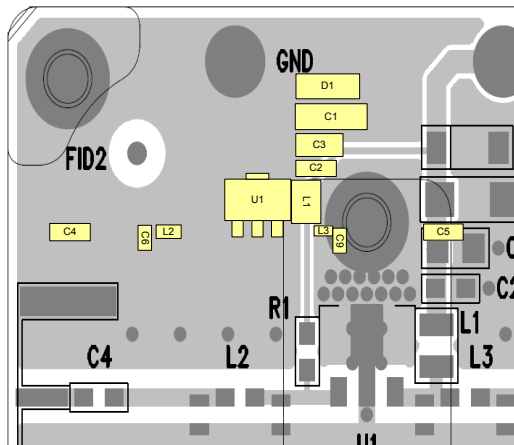


# AH118

¼ Watt, High Linearity InGaP HBT Amplifier



## Reference Design 2110-2170 MHz (AH118-89PCB2140)



**Note:**

1. The diode D1 is used as over-voltage protection on the evaluation boards. It is not specifically required in the final circuit layout in a system using a DC regulator.
2. L2 - the 0 Ω resistor - can be removed (with a thru line) in the final circuit layout.
3. The distance from U1 pin1 pad to the edge of C6 is 253 mil.
4. The distance from U1 pin3 pad to the edge of C9 is 255 mil.

### Bill of Material

Ref Des	Value	Description	Manufacturer	Part Number
U1		High Linearity Amplifier	TriQuint	AH118-89G
C1	0.1 μF	Cap, Chip, 1206, 50 V, 10%, X7R	various	
C2, C4, C5	56 pF	Cap, Chip, 0603, 50 V, 5%, NPO/COG	various	
C3	1000 pF	Cap, Chip, 0805, 50 V, 5%, NPO	various	
C6	1.8 pF	Cap, Chip, 0603, 200 V, ±0.1 pF, NPO/COG	various	
C9	1.2 pF	Cap, Chip, 0603, 200 V, ±0.1 pF, NPO/COG	various	
L1	18 nH	Ind, Chip, 0603, 5%, Ceramic Core	various	
L2	1.5 pF	Cap, Chip, 0603, 200 V, ±0.1 pF, NPO/COG	various	
L3	0 Ω	Res, 0402, Chip, 5%, 1/16 W	various	
R1		No Load Part		
D1		Zener Diode, SOD-123		



# AH118

## ¼ Watt, High Linearity InGaP HBT Amplifier

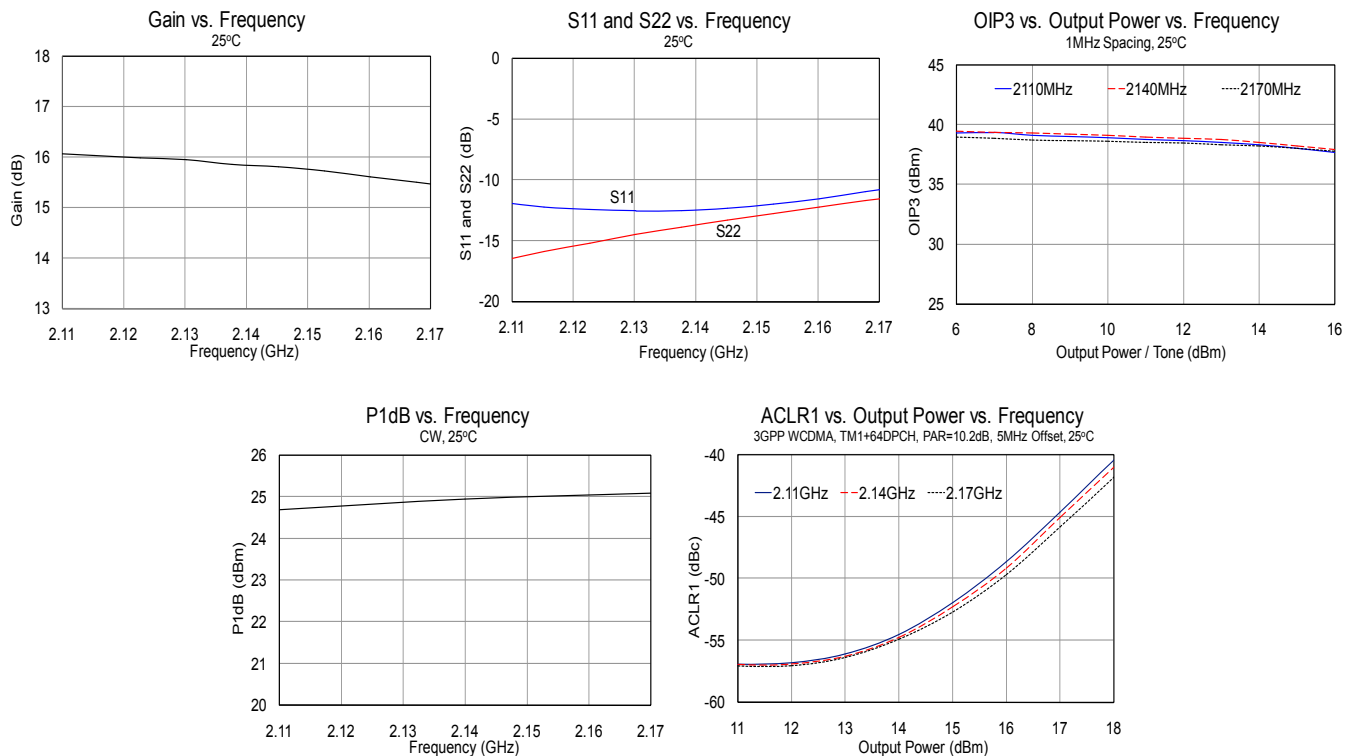


### Typical Performance 2110-2170 MHz (AH118-89PCB2140)

Frequency	MHz	2110	2140	2170
Gain [1]	dB	16.2	16.2	15.8
Input Return Loss	dB	12.4	12.3	10.4
Output Return Loss	dB	15.8	13.3	11.2
Output P1dB	dBm	24.7	24.9	25.0
Output IP3 [2]	dBm	38.8	39.0	38.5
Channel Power @ -45 dBc ACLR [3]	dBc	16.9	17.0	17.2
Noise Figure	dB	4.8	4.9	5.0
Quiescent Current , Icq	mA	160		
Device / Supply Voltage , Vcc	V	+5		

#### Notes

1. Test conditions unless otherwise noted: 25 °C, +5V, in tuned application circuit.
2. OIP3 is measured at 11 dBm Pout / tone with 1 MHz spacing.
3. ACLR test set-up: 3GPP WCDMA, TM1+64DPCH, +5MHz Offset, PAR = 10.2 dB @ 0.01% Probability.

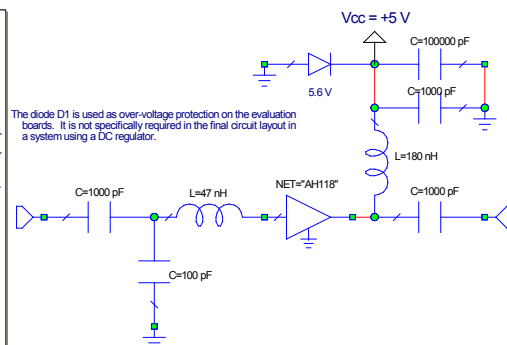
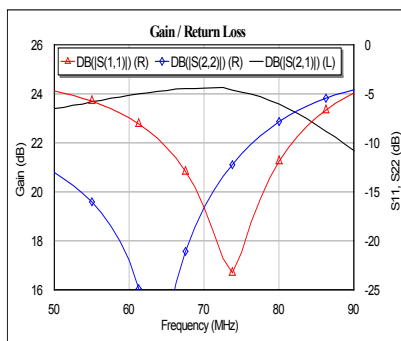


# AH118

## 1/4 Watt, High Linearity InGaP HBT Amplifier

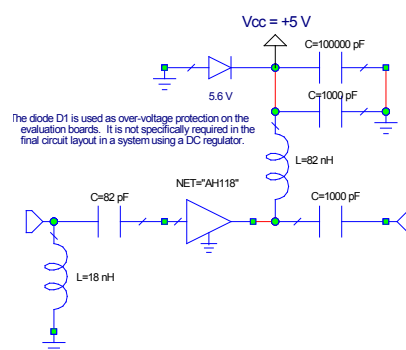
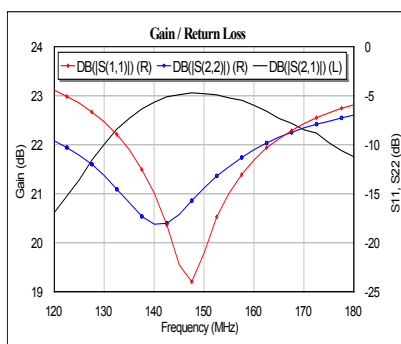
### 70 MHz Reference Design

Frequency	70 MHz
Gain	24.2 dB
Input Return Loss	17 dB
Output Return Loss	16 dB
Output P1dB	+23.6 dBm
Output IP3 (+11 dBm / tone, Δf=1 MHz)	+41 dBm
Noise Figure	4.8 dB
Supply Voltage	+5 V
Current	160 mA



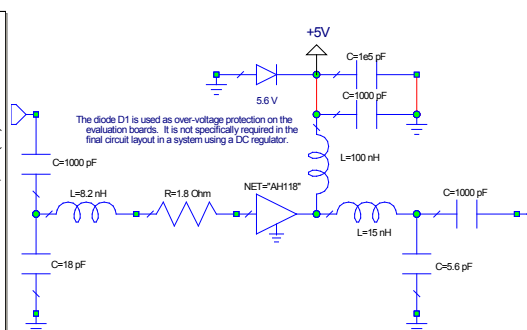
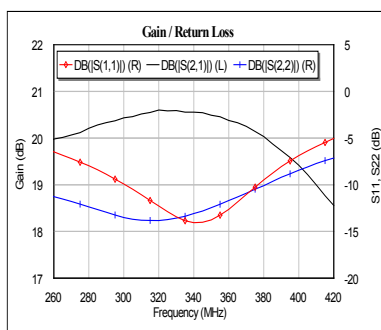
### 150 MHz Reference Design

Frequency	150 MHz
Gain	23 dB
Input Return Loss	21 dB
Output Return Loss	14 dB
Output P1dB	+23.5 dBm
Output IP3 (+11 dBm / tone, Δf=1 MHz)	+40 dBm
Noise Figure	4.9 dB
Supply Voltage	+5 V
Current	160 mA



### 340 MHz Reference Design

Frequency	340 MHz
Gain	20.6 dB
Input Return Loss	14 dB
Output Return Loss	13 dB
Output P1dB	+24 dBm
Output IP3 (+11 dBm / tone, Δf=1 MHz)	+41.4 dBm
Noise Figure	5.1 dB
Supply Voltage	+5 V
Current	160 mA



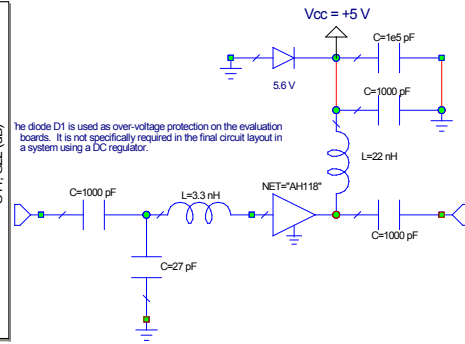
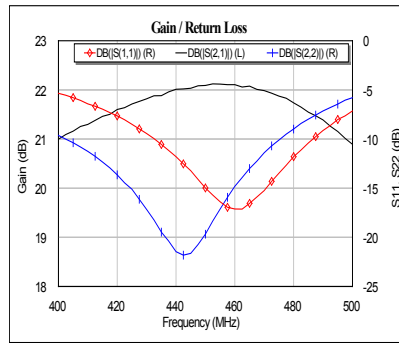
# AH118

## ¼ Watt, High Linearity InGaP HBT Amplifier



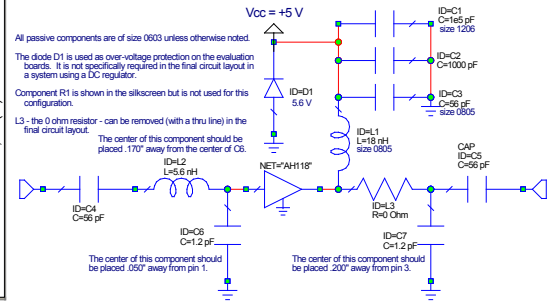
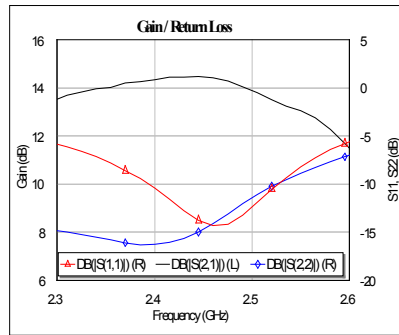
### 450 MHz Reference Design

Frequency	450 MHz
Gain	22 dB
Input Return Loss	15 dB
Output Return Loss	19 dB
Output P1dB	+24 dBm
Output IP3 (+11 dBm / tone, Δf=1 MHz)	+40 dBm
Noise Figure	5.7 dB
Supply Voltage	+5 V
Current	160 mA



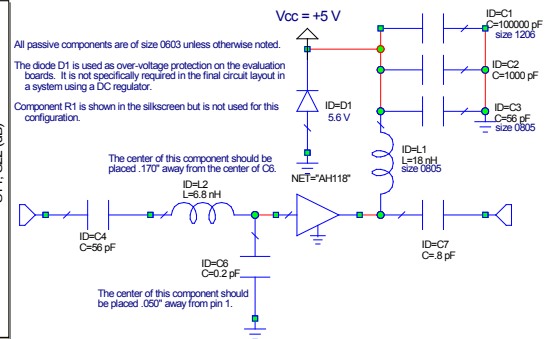
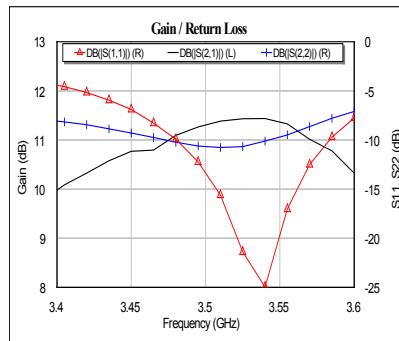
### 2450 MHz Reference Design

Frequency	2450 MHz
Gain	14.4 dB
Input Return Loss	14 dB
Output Return Loss	15 dB
Output P1dB	+25 dBm
Output IP3 (+11 dBm / tone, Δf=1 MHz)	+38 dBm
Supply Voltage	+5 V
Current	160 mA
Gain	14.4 dB



### 3500 MHz Reference Design

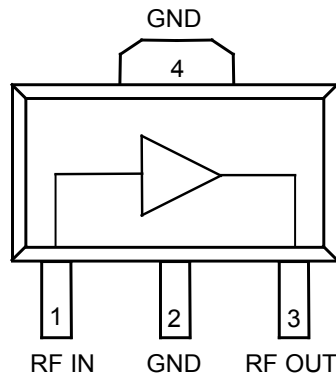
Frequency	3500 MHz
Gain	11 dB
Input Return Loss	14 dB
Output Return Loss	10 dB
Output P1dB	+23.5 dBm
Output IP3 (+11 dBm / tone, Δf=1 MHz)	+38.5 dBm
Noise Figure	5.0 dB
Supply Voltage	+5 V
Current	160 mA



# AH118

¼ Watt, High Linearity InGaP HBT Amplifier

## Pin Description



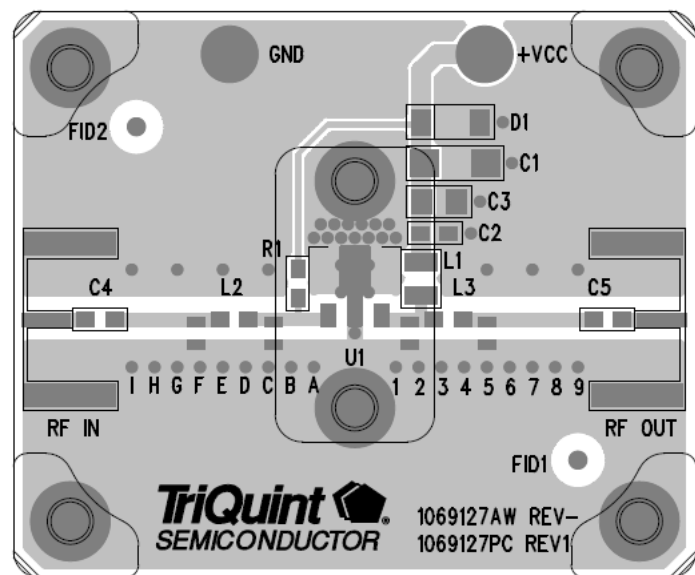
Pin	Symbol	Description
1	RF IN	RF Input. DC voltage present, blocking cap required
2	GND	No electrical connection. Provide an isolated or grounded solder pad for mounting integrity
3	RF OUT	RF Output. DC voltage present, blocking cap required
4	GND PADDLE	Multiple vias should be employed to minimize inductance and thermal resistance

## Applications Information

### PC Board Layout

Circuit Board Material: .062" total thickness with a .014" Getek top RF layer, 4 layers (other layers added for rigidity), 1 oz copper, Microstrip line details: width = .026", spacing = .026" The silk screen markers 'A', 'B', 'C', etc. and '1', '2', '3', etc. are used as placemarkers for the input and output tuning.

The pad pattern shown has been developed and tested for optimized assembly at TriQuint Semiconductor. The PCB land pattern has been developed to accommodate lead and package tolerances. Since surface mount processes vary from company to company, careful process development is recommended.



For further technical information, Refer to [http://www.triquint.com/prodserv/more\\_info/default.aspx?prod\\_id=AH118](http://www.triquint.com/prodserv/more_info/default.aspx?prod_id=AH118)



# AH118

**1/4 Watt, High Linearity InGaP HBT Amplifier**

## Product Compliance Information

### ESD Information



**Caution! ESD-Sensitive Device**

ESD Rating: Class 1A  
Value: Passes between 250 and 500V.  
Test: Human Body Model (HBM)  
Standard: JEDEC Standard JESD22-A114

### MSL Rating

Level 3 at +260 °C convection reflow  
The part is rated Moisture Sensitivity Level 3 at 260°C per JEDEC standard J-STD-020.

### Solderability

Compatible with the latest version of J-STD-020, Lead free solder, 260°

This part compliant with EU 2002/95/EC RoHS directive (Restrictions on the Use of Certain Hazardous Substances in Electrical and Electronic Equipment).

This product also has the following attributes:

- Lead Free
- Halogen Free (Chlorine, Bromine)
- Antimony Free
- TBBP-A (C<sub>15</sub>H<sub>12</sub>Br<sub>4</sub>O<sub>2</sub>) Free
- PFOS Free
- SVHC Free

## Contact Information

For the latest specifications, additional product information, worldwide sales and distribution locations, and information about TriQuint:

**Web:** [www.triquint.com](http://www.triquint.com)  
**Email:** [info-sales@tqs.com](mailto:info-sales@tqs.com)

**Tel:** +1.503.615.9000  
**Fax:** +1.503.615.8902

For technical questions and application information:

**Email:** [sjcspplications.engineering@tqs.com](mailto:sjcspplications.engineering@tqs.com)

## Important Notice

The information contained herein is believed to be reliable. TriQuint makes no warranties regarding the information contained herein. TriQuint assumes no responsibility or liability whatsoever for any of the information contained herein. TriQuint assumes no responsibility or liability whatsoever for the use of the information contained herein. The information contained herein is provided "AS IS, WHERE IS" and with all faults, and the entire risk associated with such information is entirely with the user. All information contained herein is subject to change without notice. Customers should obtain and verify the latest relevant information before placing orders for TriQuint products. The information contained herein or any use of such information does not grant, explicitly or implicitly, to any party any patent rights, licenses, or any other intellectual property rights, whether with regard to such information itself or anything described by such information.

TriQuint products are not warranted or authorized for use as critical components in medical, life-saving, or life-sustaining applications, or other applications where a failure would reasonably be expected to cause severe personal injury or death.